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Manufacturers of World Class Discrete Semiconductors

1N3070

HIGH VOLTAGE SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N3070 is a High Speed Silicon Switching Diode designed for computer and general purpose applications requiring a high breakdown voltage. For higher voltage devices refer to CSSD2003 data sheet.

MAXIMUM RATINGS ($T_A = 25^oC$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	175	V
Peak Working Reverse Voltage	V_{RWM}	175	V
Average Forward Current	I_O	200	mA
Forward Steady-State Current	I_F	500	mA
Peak Recurrent Forward Current	I_f	600	mA
Peak Forward Surge Current			
Pulse Width = 1.0s	I_{FSM}	1.0	A
Pulse Width = 1.0μs	I_{FSM}	4.0	A
Power Dissipation	P_D	500	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	^oC

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R = 175V$		100	nA
I_R	$V_R = 175V$, $T_A = 150^oC$		100	μA
BV_R	$I_R = 100\mu A$	200		V
V_F	$I_F = 100mA$		1.0	V
C_T	$V_r = 0$, $f = 1.0MHz$		5.0	pF
t_{rr}	$I_f = I_r = 30mA$, $R_L = 100\Omega$, Recovery to 1.0mA		50	ns